

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (currently amended) A via/contact photomask, comprising a first via/contact pattern serving for forming at least one first functional via/contact plug and a second via/contact pattern serving for forming at least one first dummy via/contact plug within a first dielectric layer, and the first via/contact pattern serving for forming at least one second dummy via/contact plug and the second via/contact pattern serving for forming at least one second functional via/contact plug within a second dielectric layer, wherein the via/contact photomask further comprises a third via/contact pattern serving for forming at least one third functional via/contact plug in a third dielectric layer.

2. (cancelled)

3. (original) The via/contact photomask of claim 1, wherein the via/contact photomask is applied in two consecutive via/contact photolithographic processes.

4. (withdrawn) A structure of interconnection between two metals within an integrated circuit, comprising:

a first metal pattern comprising a first metal structure and a second metal structure;

a first via/contact plug on the first metal structure of the first metal pattern and a second via/contact plug on the second metal structure of the first metal pattern; and

a second metal pattern comprising a first metal structure on the first via/contact plug and a second metal structure on the second via/contact plug, wherein the first metal structures of the first and second metal patterns are functional, and at least one of the second metal structures of the first and second metal patterns is dummy.

5. (withdrawn) The structure of the claim 4, wherein the first and second via/contact plugs are formed by utilizing a via/contact photomask which comprises a first via/contact pattern serving for forming the first via/contact plug and a second via/contact pattern serving for forming the second via/contact plug.

6. (withdrawn) The structure of the claim 4, wherein the first metal structures of the first and second metal patterns are metal lines, and the at least one of the second metal structures of the first and second metal patterns is a metal island.

7. (withdrawn) A method of forming interconnection within an integrated circuit, comprising:

forming a first dielectric layer over a first metal pattern formed on a substrate, the first dielectric layer having first via/contact plugs therein formed by using a via/contact photomask for patterning first via/contact holes;

forming a second metal pattern over the first dielectric layer and on the first via/contact plugs; and

forming a second dielectric layer over the second metal pattern, the second dielectric layer having second via/contact plugs therein formed by using the via/contact photomask for patterning second via/contact holes.

8. (withdrawn) The method of claim 7, wherein the via/contact photomask comprises a first via/contact pattern serving for forming the first via/contact plugs within the first dielectric layer and the second via/contact pattern serving for forming the second via/contact plugs within the second dielectric layer.

9. (withdrawn) The method of claim 7, wherein the first metal pattern comprises a first metal structure and a second metal structure, the second metal pattern comprises a first metal structure and a second metal structure, and the first metal structures of the first and second metal patterns are functional, and at least one of the second metal structures of the first and second metal patterns is dummy.

10. (withdrawn) The method of claim 9, wherein the first metal structures of the first and second metal patterns are metal lines, and the at least one of the second metal structures of the first and second metal patterns is a metal island.

11. (withdrawn) The method of claim 7, wherein the via/contact photomask is applied in two consecutive via/contact photolithographic processes.